

GENERAL PURPOSE APPLICATION.

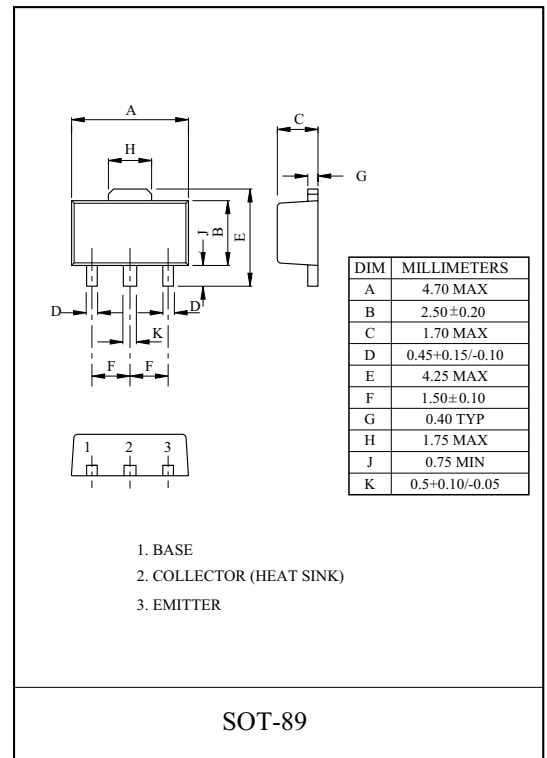
FEATURES

- 1W (Mounted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTB1260.

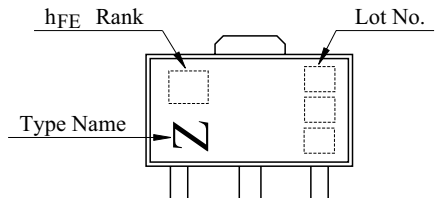
MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1	A
Emitter Current	I_E	-1	A
Collector Power Dissipation	P_C	500	mW
	P_C^*	1	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 ~ 150	℃

* Mounted on ceramic substrate (250mm² × 0.8t)



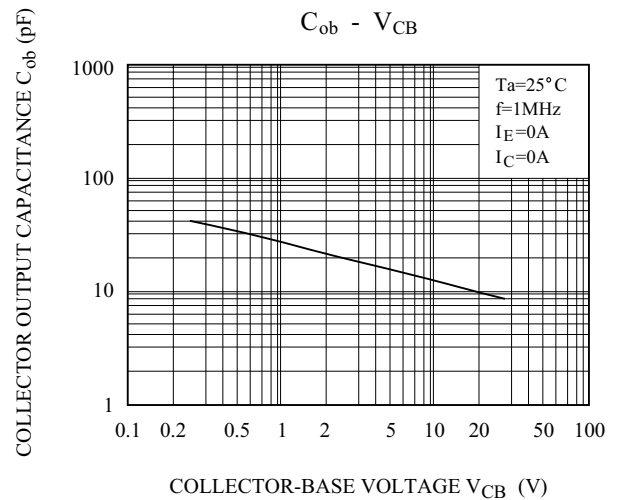
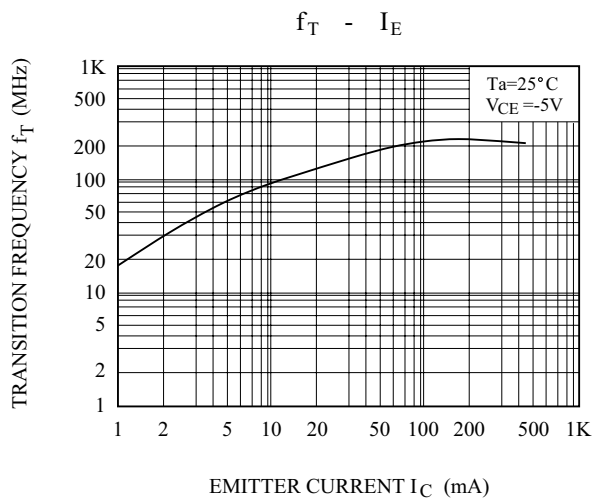
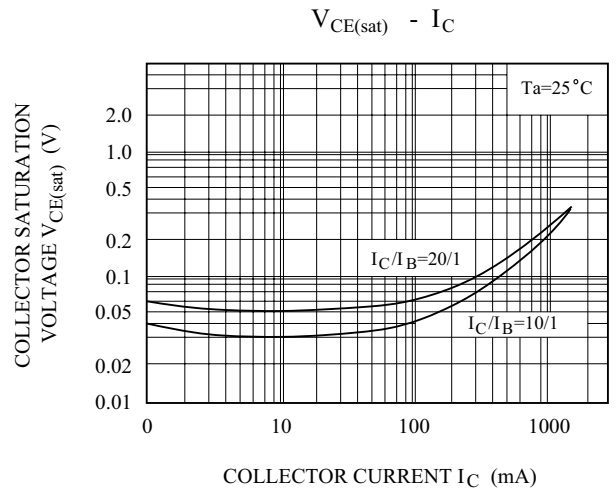
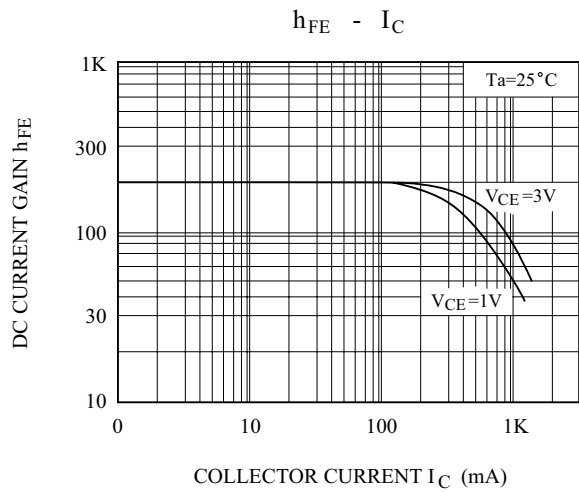
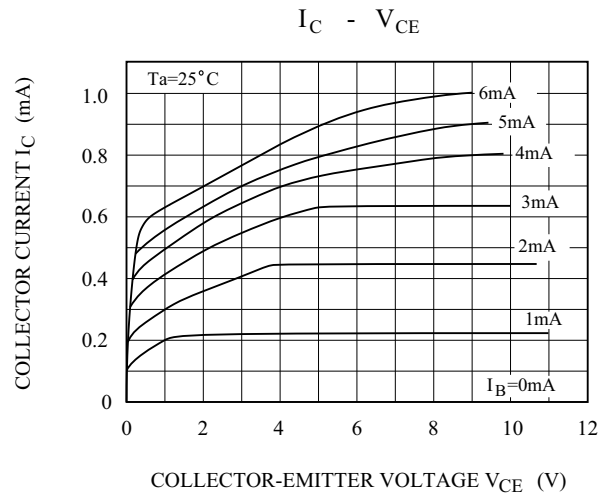
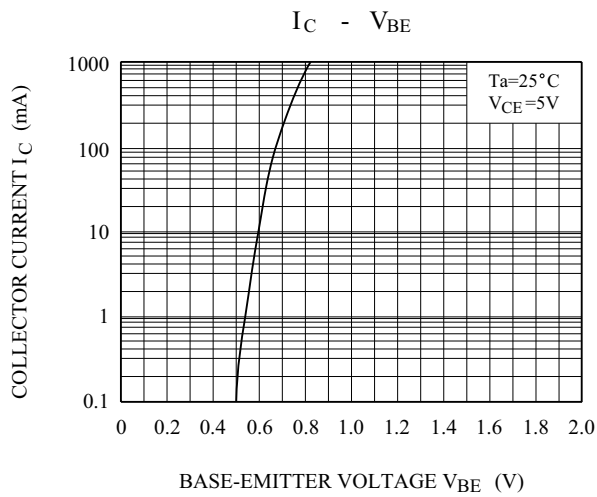
Marking



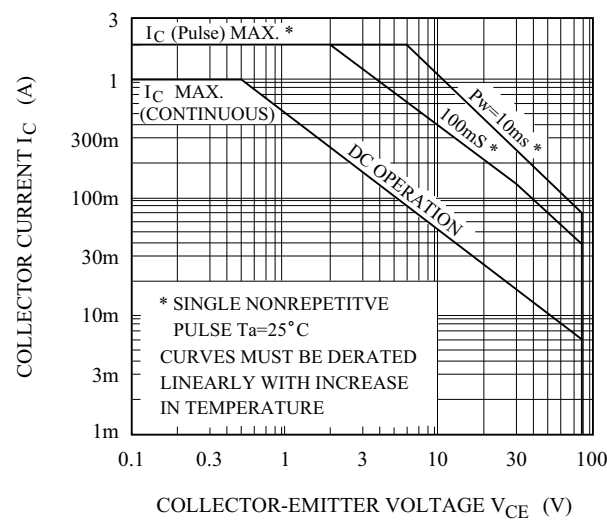
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=80V, I_E=0$	-	-	1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=4V, I_C=0$	-	-	1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	80	-	-	V
DC Current Gain	$h_{FE}(\text{Note})$	$V_{CE}=3V, I_C=500mA$	70	-	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=20mA$	-	-	0.4	V
Transition Frequency	f_T	$V_{CE}=10V, I_C=50mA, f=100MHz$	-	100	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	20	-	pF

Note : h_{FE} Classification O:70 ~ 140, Y:120 ~ 240, GR:200 ~ 400



SAFE OPERATING AREA



Pc - Ta

